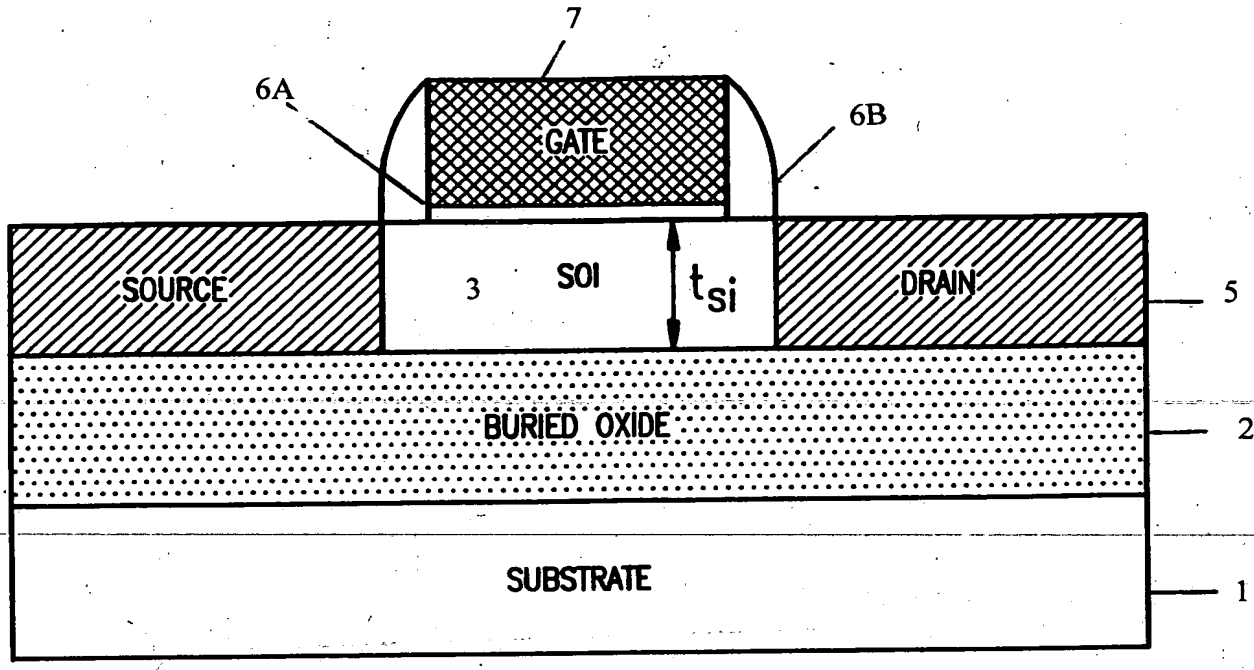


FIG.1

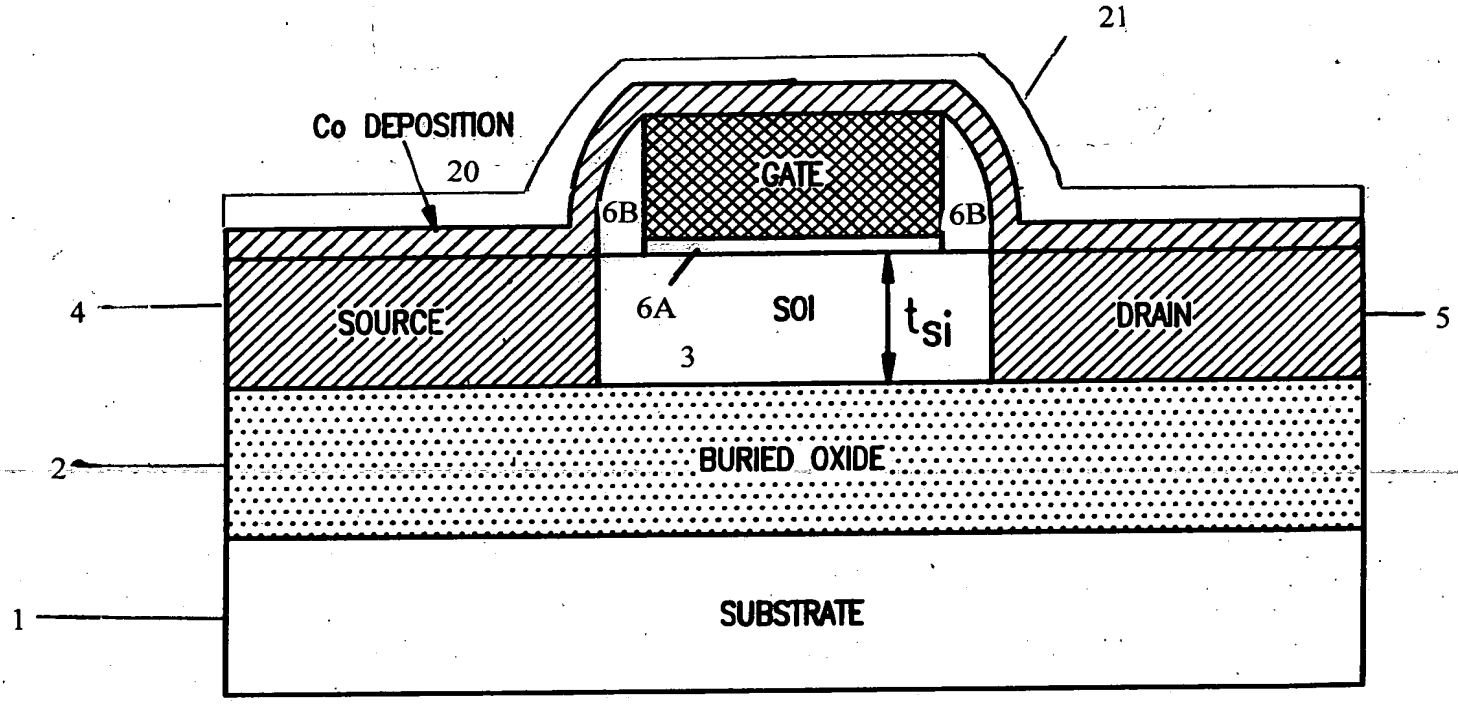


FIG.2

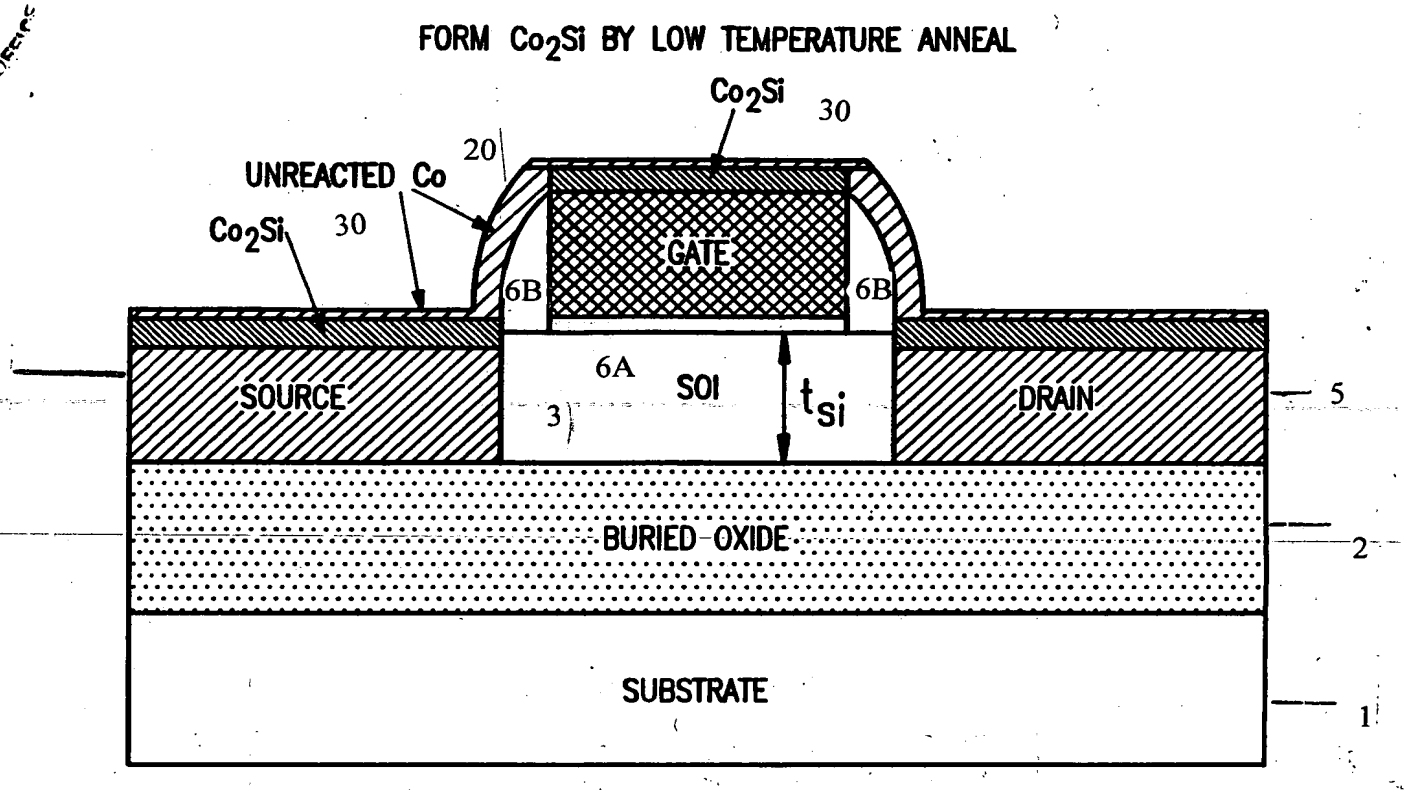


FIG.3

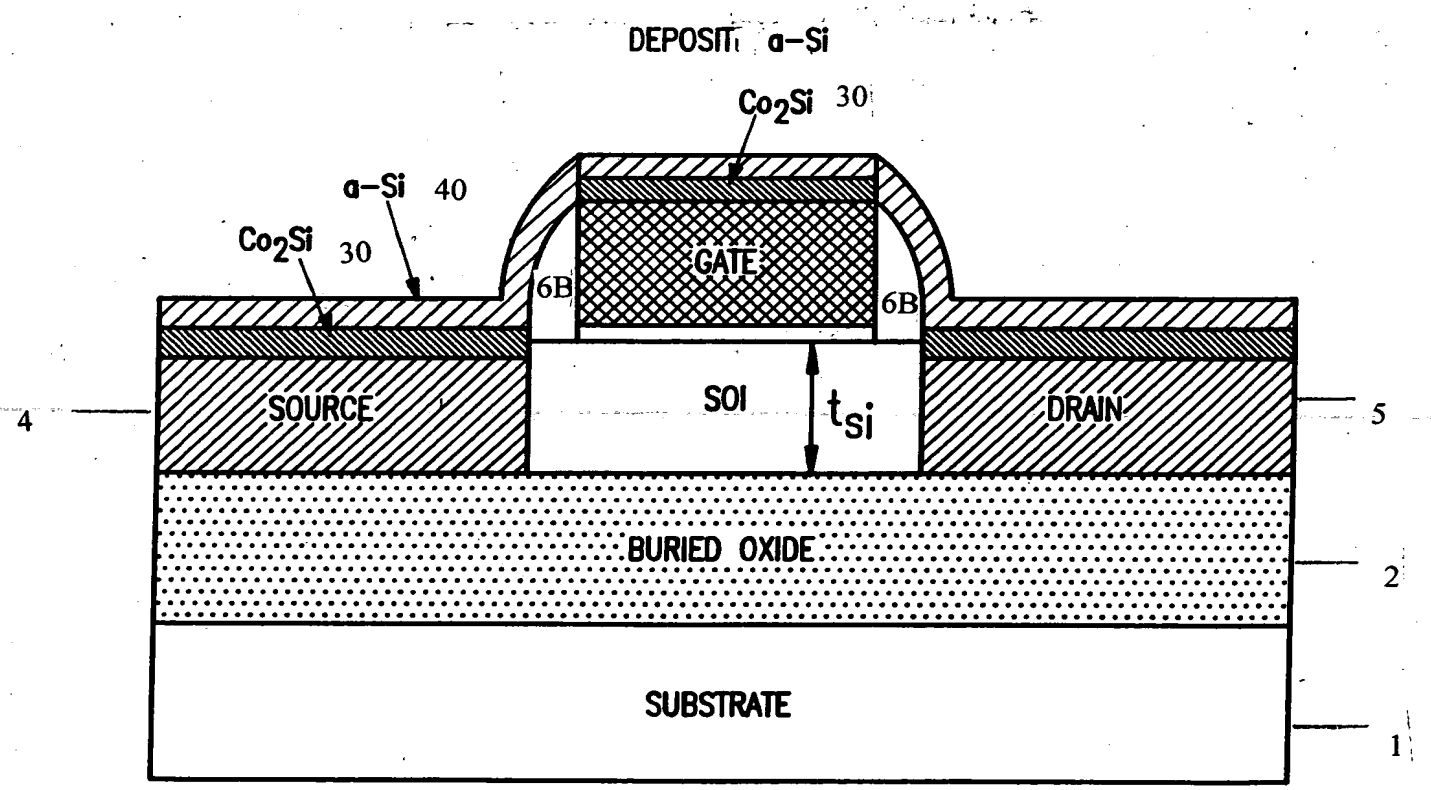


FIG.4

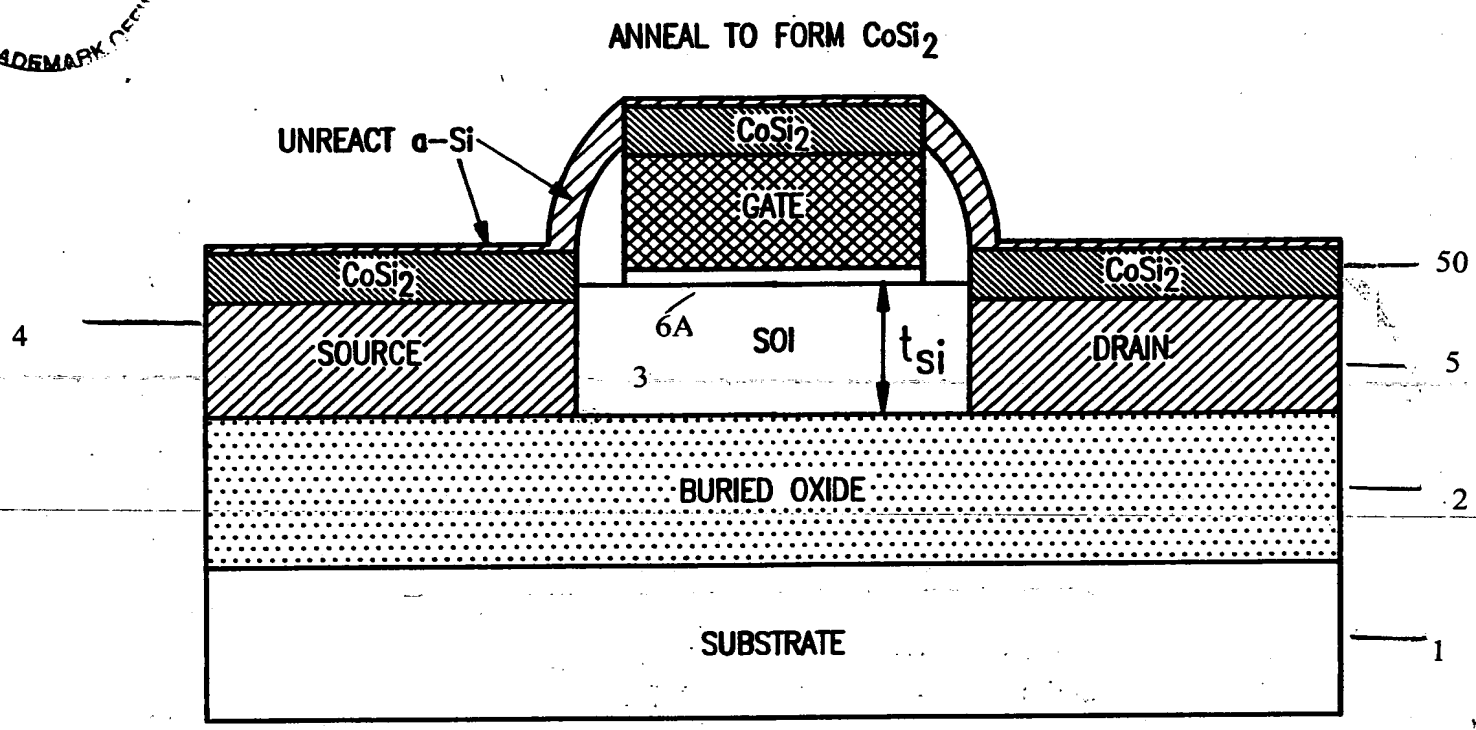


FIG.5

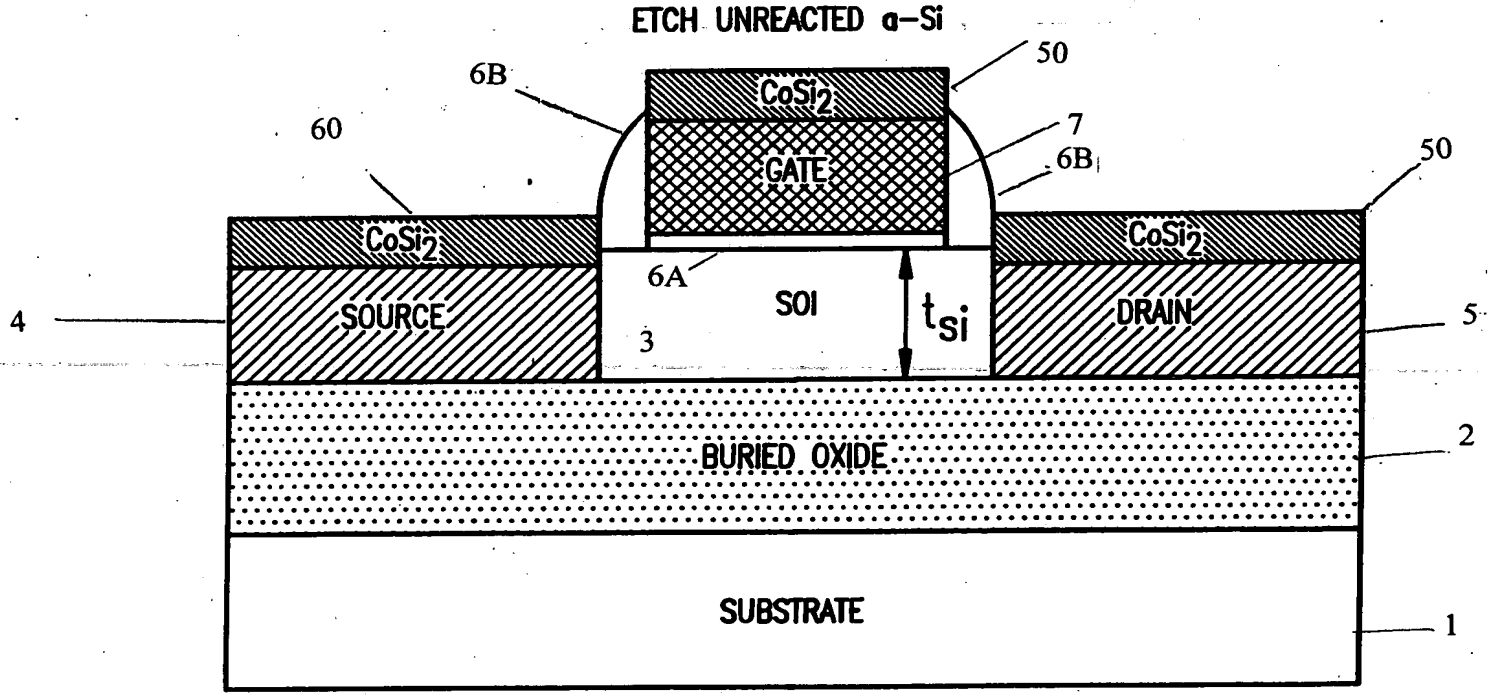


FIG.6

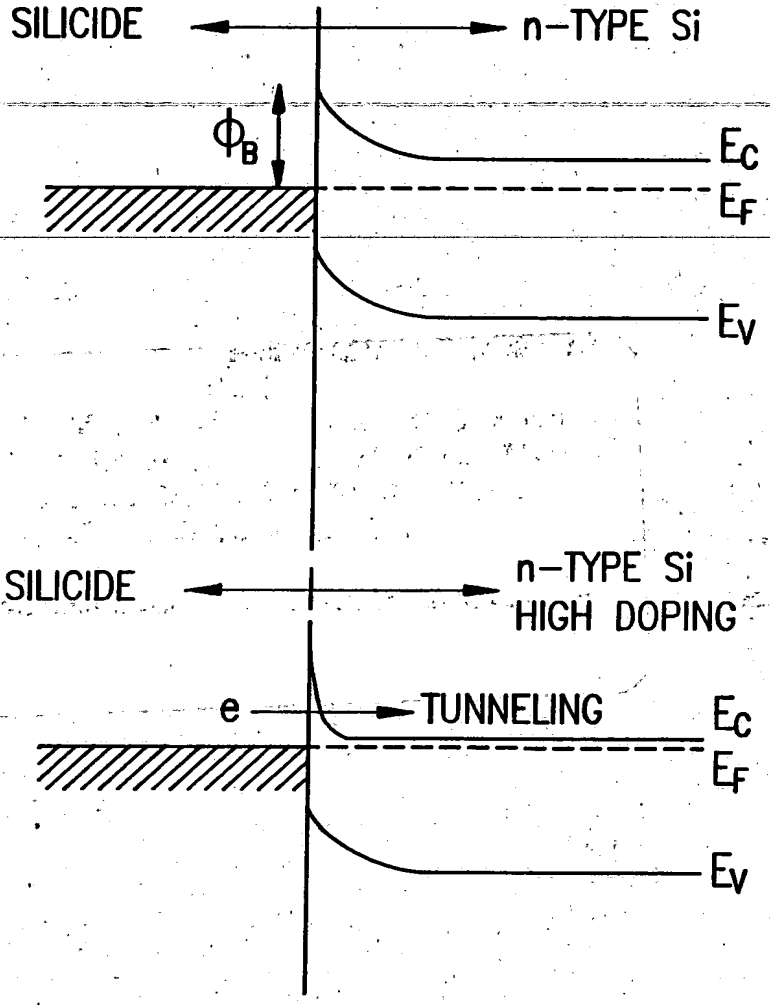
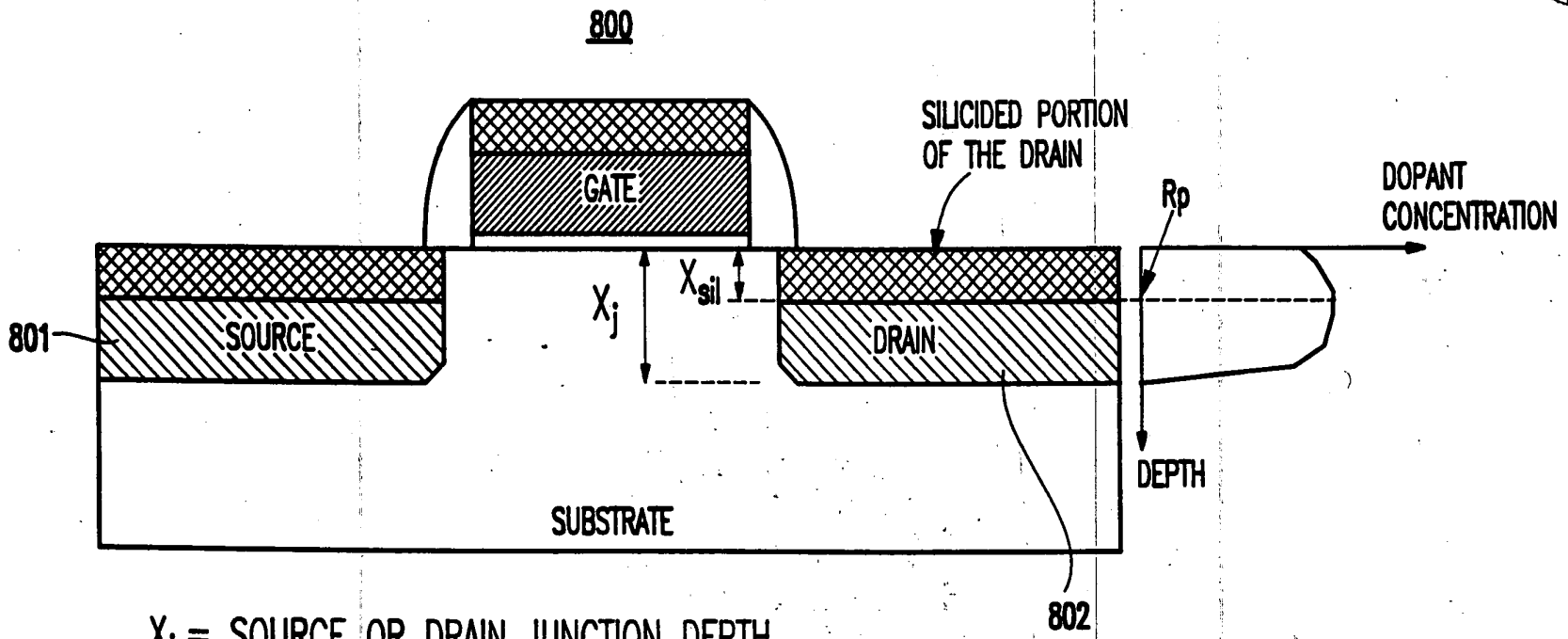


FIG.7A

FIG.7B



X_j = SOURCE OR DRAIN JUNCTION DEPTH

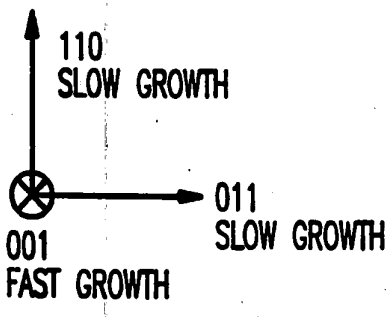
X_{sil} = SILICIDE JUNCTION DEPTH

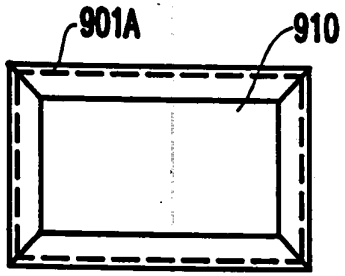
Rp = PEAK DOPANT CONCENTRATION

REQUIREMENTS:

1. $X_j > X_{sil}$
2. X_{sil} ROUGHLY EQUALS Rp

FIG.8





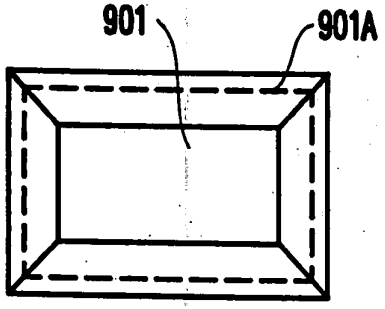
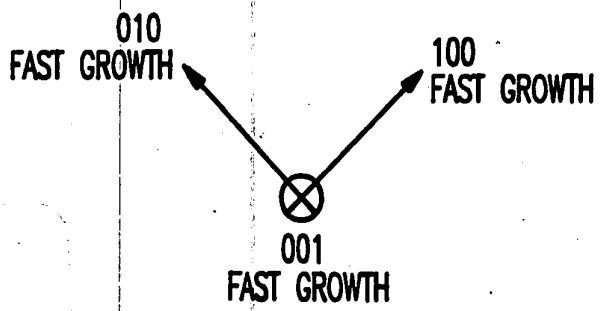
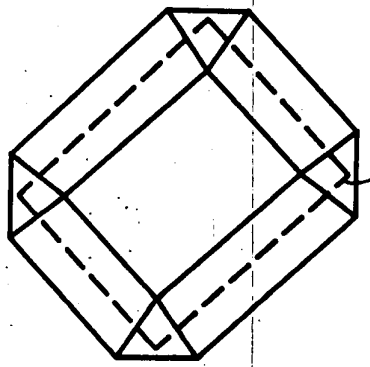
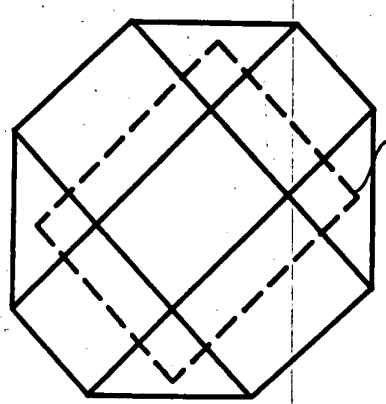


FIG.9A





$t_{GROWTH}=t1$



$t_{GROWTH}=t2>t1$

THE DASHED LINE
SHOWS THE INITIAL GROWTH
WINDOW WHICH IS
DEFINED BY THE HARD MASK

FIG.9B